

KS54AHCT 843/844
KS74AHCT

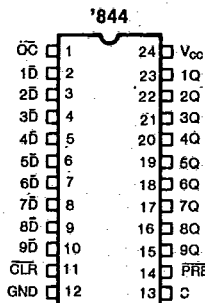
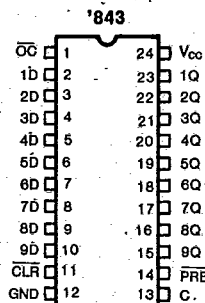
9-Bit Bus Interface D-Type Latches with 3-State Outputs

T-46-07-05

FEATURES

- Bus-Structured Pinout
- Provide Extra Bus Driving Latches Necessary for Wider Address/Data Paths or Buses with Parity
- Power-Up High Impedance
- Function, pin-out, speed and drive compatibility with 54/74ALS logic family
- Low power consumption characteristic of CMOS
- 3-State outputs with high drive current (I_{OL} = 24 mA @ V_{OL} = 0.5V) for direct bus interface
- Inputs and outputs interface directly with TTL, NMOS and CMOS devices
- Wide operating voltage range: 4.5V to 5.5V
- Characterized for operation over industrial and military temperature ranges:
 KS74AHCT: -40°C to +85°C
 KS54AHCT: -55°C to +125°C
- Package options include plastic "small outline" packages, standard plastic and ceramic 300-mil DIPs

PIN CONFIGURATIONS



DESCRIPTION

These 9-bit bus interface latches feature three-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. They are suitable for implementing wider buffer registers, I/O ports, bidirectional bus drivers and working registers.

The nine latches are transparent D-type. The '843 has noninverting data (D) inputs and the '844 has inverting \bar{D} inputs.

A buffered output control (\overline{OC}) input can be used to place the nine outputs in either a normal logic state (high or low levels) or a high-impedance state. The high-impedance state and increased drive provide the capability to drive the bus lines in a bus-organized system without need for interface or pull-up components.

The output control (\overline{OC}) does not affect the internal operation of the flip-flops. Old data can be retained or new data can be entered while the outputs are off.

These devices provide speeds and drive capability equivalent to their ALSTTL counterparts and yet maintain CMOS power levels. The input and output voltage levels allow direct interface with TTL, NMOS and CMOS devices without any external components.

All inputs and outputs are protected from damage due to static discharge by internal diode clamps to V_{CC} and ground.

FUNCTION TABLES

'843

INPUTS					OUTPUT
PRE	CLR	\overline{OC}	C	D	Q
L	X	L	X	X	H
H	L	L	X	X	L
H	H	L	H	L	L
H	H	L	H	H	H
H	H	L	L	X	Q ₀
X	X	H	X	X	Z

'844

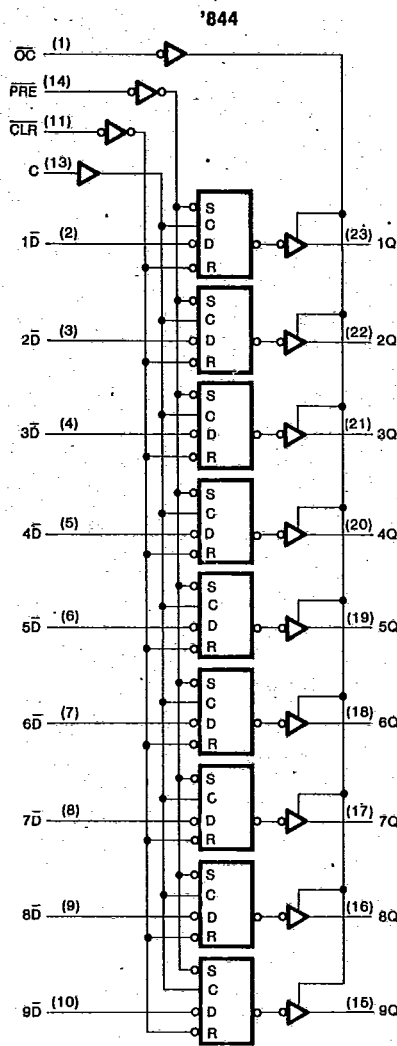
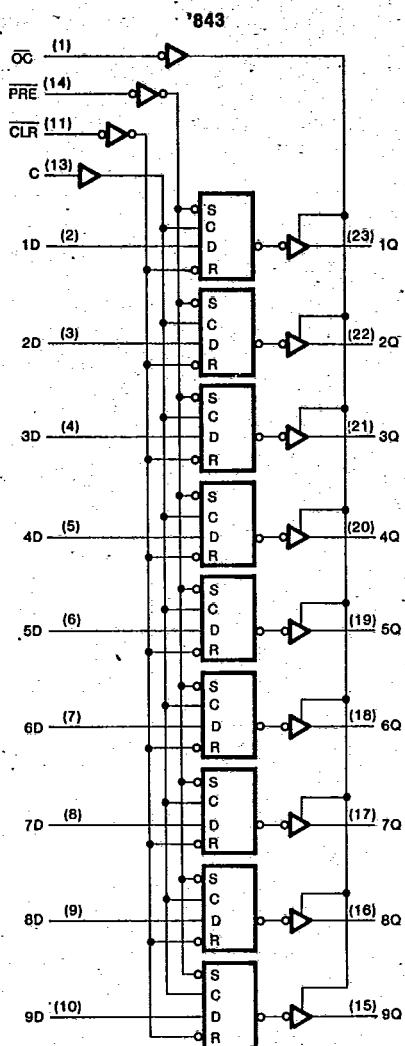
INPUTS					OUTPUT
PRE	CLR	\overline{OC}	C	\bar{D}	Q
L	X	L	X	X	H
H	L	L	X	X	L
H	H	L	H	L	H
H	H	L	H	H	L
H	H	L	L	X	Q ₀
X	X	H	X	X	Z

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LOGIC DIAGRAMS



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Absolute Maximum Ratings*

Supply Voltage Range V_{CC} , -0.5V to +7V
 DC Input Diode Current, I_{IK}
 ($V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$) ± 20 mA
 DC Output Diode Current, I_{OK}
 ($V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$) ± 20 mA
 Continuous Output Current Per Pin, I_O
 ($-0.5V < V_O < V_{CC} + 0.5V$) ± 70 mA
 Continuous Current Through
 V_{CC} or GND pins' ± 250 mA
 Storage Temperature Range, T_{stg} -65°C to +150°C
 Power Dissipation Per Package, P_d † 500 mW

* Absolute Maximum Ratings are those values beyond which permanent damage to the device may occur. These are stress ratings only and functional operation of the device at or beyond them is not implied. Long exposure to these conditions may affect device reliability.

† Power Dissipation temperature derating:
 Plastic Package (N): -12mW/°C from 65°C to 85°C
 Ceramic Package (J): -12mW/°C from 100°C to 125°C

Recommended Operating Conditions

Supply Voltage, V_{CC} 4.5V to 5.5V
 DC Input & Output Voltages*, V_{IN} , V_{OUT} 0V to V_{CC}
 Operating Temperature
 Range KS74AHCT: -40°C to +85°C
 KS54AHCT: -55°C to +125°C
 Input Rise & Fall Times, t_r , t_f Max 500 ns
 * Unused inputs must always be tied to an appropriate logic voltage level (either V_{CC} or GND)

DC ELECTRICAL CHARACTERISTICS ($V_{CC}=5V \pm 10\%$ Unless Otherwise Specified)

Characteristic	Symbol	Test Conditions	$T_a = 25^\circ C$			Unit	
			Typ	KS74AHCT $T_a = -40^\circ C$ to $+85^\circ C$	KS54AHCT $T_a = -55^\circ C$ to $+125^\circ C$		Guaranteed Limits
Minimum High-Level Input Voltage	V_{IH}			2.0	2.0	2.0	V
Maximum Low-Level Input Voltage	V_{IL}			0.8	0.8	0.8	V
Minimum High-Level Output Voltage	V_{OH}	$V_{IN}=V_{IH}$ or V_{IL} $I_O = -20\mu A$ $I_O = -6mA$	V_{CC} 4.2	$V_{CC} - 0.1$ 3.98	$V_{CC} - 0.1$ 3.84	$V_{CC} - 0.1$ 3.7	V
Maximum Low-Level Output Voltage	V_{OL}	$V_{IN}=V_{IH}$ or V_{IL} $I_O = 20\mu A$ $I_O = 12mA$ $I_O = 24mA$	0	0.1 0.26 0.39	0.1 0.33 0.5	0.1 0.4	V
Maximum Input Current	I_{IN}	$V_{IN}=V_{CC}$ or GND		± 0.1	± 1.0	± 1.0	μA
Maximum 3-State Leakage Current	I_{OZ}	Output Enable $= V_{IH}$ $V_{OUT}=V_{CC}$ or GND		± 0.5	± 5.0	± 10.0	μA
Maximum Quiescent Supply Current	I_{CC}	$V_{IN}=V_{CC}$ or GND $I_{OUT}=0\mu A$		8.0	80.0	160.0	μA
Additional Worst Case Supply Current	ΔI_{CC}	per input pin $V_I = 2.4V$ other inputs: at V_{CC} or GND $I_{OUT}=0\mu A$		2.7	2.9	3.0	mA

KS54AHCT **843/844**
KS74AHCT**9-Bit Bus Interface D-Type
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AC ELECTRICAL CHARACTERISTICS (Input $t_r, t_f \leq 2$ ns), AHCT843, AHCT844

Characteristic	Symbol	Conditions†	$T_a = 25^\circ\text{C}$	KS74AHCT		KS54AHCT		Unit
			$V_{CC} = 5.0\text{V}$	$T_a = -40^\circ\text{C to } +85^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 10\%$		$T_a = -55^\circ\text{C to } +125^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 10\%$		
			Typ	Min	Max	Min	Max	
Propagation Delay, Data to Q	t_{PLH}	$C_L = 50\text{pF}$ $C_L = 150\text{pF}$	13 16		18 23		22 28	ns
	t_{PHL}	$C_L = 50\text{pF}$ $C_L = 150\text{pF}$	13 16		18 23		22 28	
Propagation Delay, C to any Q	t_{PLH}	$C_L = 50\text{pF}$ $C_L = 150\text{pF}$	16 19		26 31		31 37	ns
	t_{PHL}	$C_L = 50\text{pF}$ $C_L = 150\text{pF}$	16 19		26 31		31 37	
Propagation Delay, PRE to Q	t_{PLH}	$C_L = 50\text{pF}$ $C_L = 150\text{pF}$	17 20		27 32		32 38	ns
Propagation Delay, CLR to Q	t_{PHL}	$C_L = 50\text{pF}$ $C_L = 150\text{pF}$	17 20		27 32		32 38	ns
Output Enable Time, OC to any Q	t_{PZL}	$R_L = 1\text{k}\Omega$ $C_L = 50\text{pF}$ $C_L = 150\text{pF}$ $C_L = 150\text{pF}$	11 14		18 23		22 28	ns
	t_{PZL}		11 14		18 23		22 28	
Output Disable Time, OC to any Q	t_{PHZ}	$R_L = 1\text{k}\Omega$	13		18		22	ns
	t_{PLZ}	$C_L = 50\text{pF}$	13		18		22	
Pulse Width, C High	t_w		12	20		25		ns
Setup Time, Data before C \downarrow	t_{SU}		8	10		12		ns
Hold Time, Data after C \downarrow	t_H		3	5		7		ns
Input Capacitance	C_{IN}		5					pF
Output Capacitance	C_{OUT}	Output Disabled	10					pF
Power Dissipation Capacitance* (per stage)	C_{PD}	OC = V_{CC}	5					pF
		OC = GND	30					

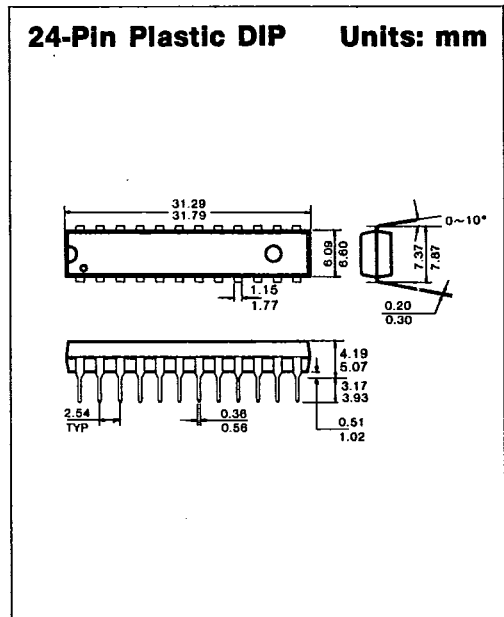
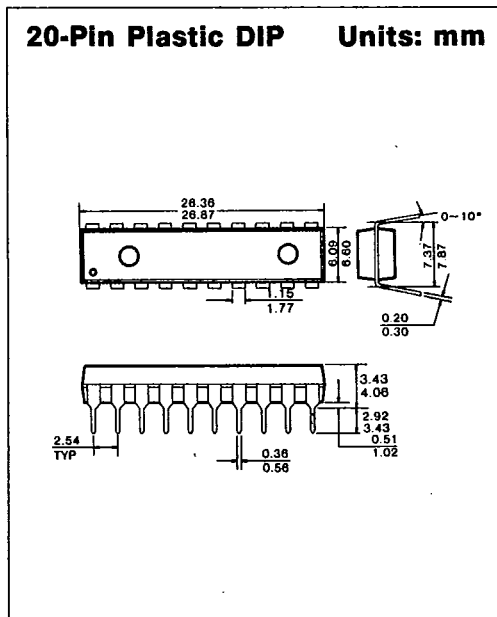
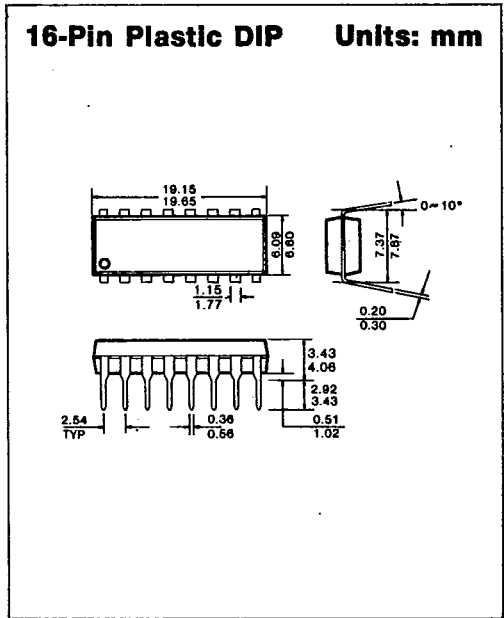
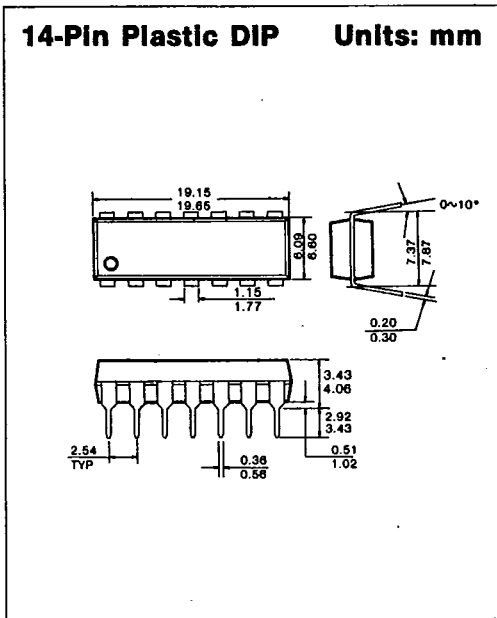
* C_{PD} determines the no-load dynamic power dissipation: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

† For AC switching test circuits and timing waveforms see section 2.

PACKAGE DIMENSIONS

T-90-20

1. PLASTIC PACKAGES



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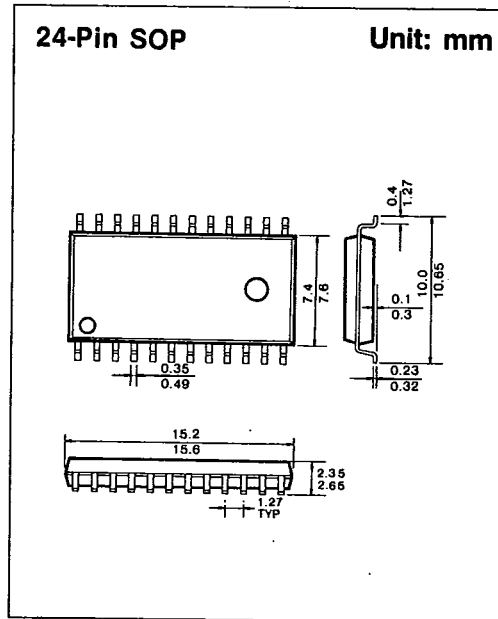
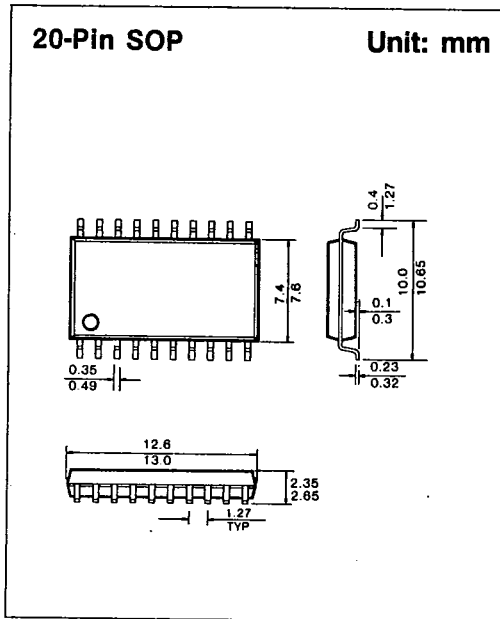
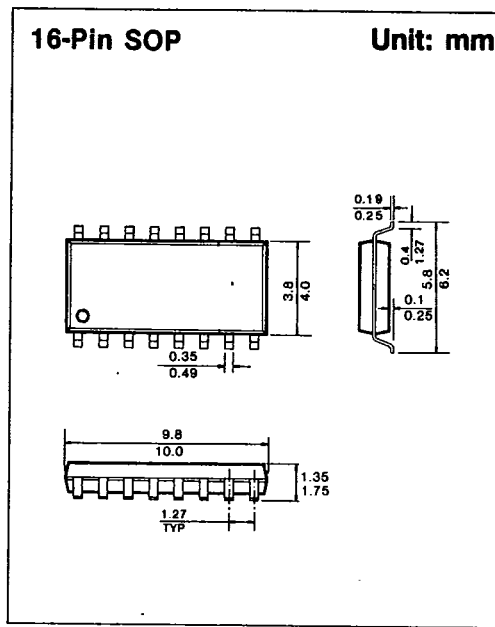
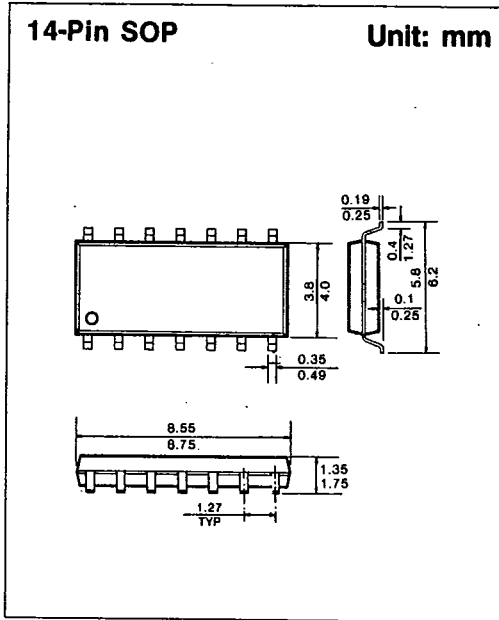
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PACKAGE DIMENSIONS

T-90-20



PACKAGE DIMENSIONS

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2. CERAMIC PACKAGES

14-Pin Ceramic DIP Units: mm

Dim	Millimeters	
	Min	Max
A	—	5.08
B	0.38	0.58
B ₁	1.40	1.78
C	0.20	0.38
D	18.16	19.56
E	8.10	7.49
E ₁	7.82	10.03
F	2.54	
L	3.18	4.19
Q	0.51	1.02
S	1.91	2.29

16-Pin Ceramic DIP Units: mm

Dim	Millimeters	
	Min	Max
A	—	5.08
B	0.38	0.58
B ₁	1.40	1.78
C	0.20	0.38
D	19.05	19.94
E	8.10	7.49
E ₁	7.82	10.03
F	2.54	
L	3.18	4.19
Q	0.51	1.02
S	0.51	1.14

20-Pin Ceramic DIP Units: mm

Dim	Millimeters	
	Min	Max
A	4.06	5.08
B	0.38	0.53
B ₁	1.14	1.52
C	0.20	0.38
D	25.78	26.33
E	8.10	8.60
E ₁	7.77	7.95
F	2.54	
L	3.73	4.01
Q	0.38	0.89
S	0.51	1.14

24-Pin Ceramic DIP Units: mm

Dim	Millimeters	
	Min	Max
A	4.06	5.08
B	0.38	0.53
B ₁	1.14	1.52
C	0.20	0.38
D	31.50	32.84
E	7.24	7.75
E ₁	7.77	7.98
F	2.54	
L	3.73	4.01
Q	0.508	1.776
S	1.85	1.93

